

Umer Farooq Ahmed

List of Publications by Year in descending order

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Version: 2024-02-01

17
papers

62
citations

1684188

5
h-index

1720034

7
g-index

17
all docs

17
docs citations

17
times ranked

56
citing authors

#	ARTICLE	IF	CITATIONS
1	A Schrödinger-Poisson model for output characteristics of trigate ballistic Si fin field effect transistors (FinFETs). International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2022, 35, e2927.	1.9	4
2	A Unified Depletion/Inversion Model for Heterojunction Trigate FinFETs DC Characteristics. IEEE Access, 2021, 9, 89768-89777.	4.2	0
3	An improved model to predict DC characteristics of organic field-effect transistors. Journal of Computational Electronics, 2021, 20, 2342-2349.	2.5	0
4	A modified analytical model for AlGaIn/GaN FinFETs I_D characteristics. Semiconductor Science and Technology, 2020, 35, 035002.	2.0	4
5	Design and Development of Control System for Unmanned Ground Vehicle and its Manipulator. , 2020, , .		2
6	An improved temperature dependent analytical model to predict AlGaIn/GaN high electron mobility transistors AC characteristics. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2019, 32, e2648.	1.9	1
7	Temperature Dependent Analytical DC Model for Wide Bandgap MESFETs. IEEE Access, 2019, 7, 49702-49711.	4.2	4
8	A 3-D potential model to assess DC characteristics of Si FinFETs. Journal of Computational Electronics, 2019, 18, 893-905.	2.5	8
9	An analytical model to assess DC characteristics of independent gate Si FinFETs. Turkish Journal of Electrical Engineering and Computer Sciences, 2019, 27, 2456-2465.	1.4	1
10	An Improved Technique to Assess AC Performance of a Submicron GaN HEMTs. , 2019, , .		0
11	Non-linear compact model for FinFETs output characteristics. IET Circuits, Devices and Systems, 2019, 13, 1249-1254.	1.4	2
12	Simulation and comparative analysis of the DC characteristics of submicron GaN HEMTs for use in CAD software. Journal of Computational Electronics, 2019, 18, 482-491.	2.5	4
13	A global parameters extraction technique to model organic field effect transistors output characteristics. Solid-State Electronics, 2019, 152, 81-92.	1.4	7
14	An improved space charge distribution analytical model to assess field-effect transistor's intrinsic capacitors. Turkish Journal of Electrical Engineering and Computer Sciences, 2019, 27, 4502-4517.	1.4	1
15	An improved model to assess temperature-dependent DC characteristics of submicron GaN HEMTs. Journal of Computational Electronics, 2018, 17, 653-662.	2.5	14
16	Assessment of intrinsic small signal parameters of submicron SiC MESFETs. Solid-State Electronics, 2018, 139, 80-87.	1.4	5
17	An improved model for the I_D - V characteristics of submicron SiC MESFETs by evaluating the potential distribution inside the channel. Journal of Computational Electronics, 2017, 16, 514-525.	2.5	5